

XRT8010

350MHZ CLOCK & CRYSTAL MULTIPLIER WITH LVDS OUTPUTS

DECEMBER 2002

DESCRIPTION

The XRT8010 is a monolithic analog phase locked loop that provides a high frequency LVDS clock output, using a low frequency crystal or reference clock. It is designed for SONET/SDH and other low jitter applications. The high performance of the IC provides a very low jitter LVDS clock output up to 350 MHz, while operating at 3.3 volts. The XRT8010 has a selectable 8x or 16x internal multiplier for an external crystal or signal source. The Output Enable pin provides a true disconnect for the LVDS output. The very compact (4 x 4 mm) low inductance package is ideal for high frequency operation.

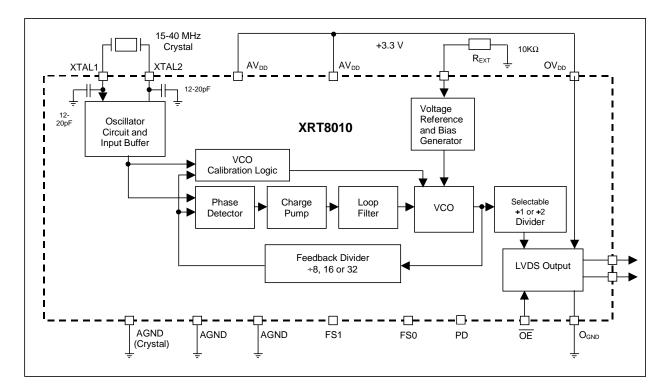
APPLICATIONS

- Gigabit Ethernet
- SONET/SDH
- SPI-4 Phase 2
- Voltage Controlled Crystal Oscillator (VCXO)
- 8x or 16x Clock Multiplier
 - Computer Systems
 - Telecommunication systems

FIGURE 1. XRT8010 BLOCK DIAGRAM

FEATURES

- Up to 350 MHz operation
- Low Output Jitter:
 - 6 ps rms at 312 MHz, input referred
- On Chip Crystal Oscillator Circuit
 - Optimized for 15 to 40 MHz crystals
 - Uses parallel fundamental mode
- Selectable 8x or 16x multiplier
- Selectable ÷1 or ÷2 LVDS output
- LVDS output meets TIA/EIA 644A Specification (2001)
- 3.3V Low power CMOS: <80 mW typical
- -40°C to +85°C operating temperature
- Extremely small 16-lead QFN package



REV. P1.0.0



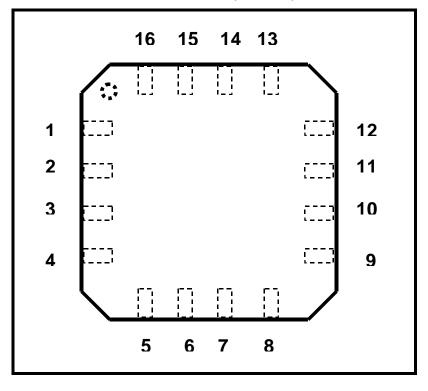
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PRELIMINARY

XRT8010 PIN DESCRIPTION

PIN #	NAME	Түре	DESCRIPTION		
1	AVDD		+ 3.3V Analog Supply for Crystal Oscillator		
2	AGND		Analog Ground for Crystal Oscillator		
3	XTAL1	I	Crystal pin 1 or external clock input		
4	XTAL2	0	Crystal pin 2 (output drive for crystal)		
5	AGND		Analog Ground		
6	REXT	I	External Bias Resistor ($10K\Omega$ to ground)		
7	OE	I	Output Enable, Active low (Internal 50K Ω pull-down to ground)		
8	PD	I	Power Down, Active High (Internal 50K Ω pull-down to ground)		
9	FS1	I	Frequency select "1" (Internal 50K Ω pull-down to ground)		
10	FS0	I	Frequency select "0" (Internal 50K Ω pull-up to VDD)		
11	AGND		Analog Ground		
12	OGND		Output Ground for LVDS outputs		
13	OUTN	0	LVDS negative output for 50Ω line		
14	OUTP	0	LVDS positive output for 50Ω line		
15	OVDD		+ 3.3V Digital Supply for LVDS Output buffer		
16	AVDD		+ 3.3V Analog Supply		

FIGURE 2. PIN-OUT OF THE XRT8010 (TOP VIEW)



ABSOLUTE MAXIMUM RATINGS

Supply voltage	-0.5 to 6.0 V		
VIN	-0.5 to 6.0 V		
Storage Temperature	-65°C to + 150°C		
Operating Temperature	-40°C to + 85°C		
ESD	2,000 volts		

ELECTRICAL SPECIFICATIONS:

PARAMETER	SYMBOL	Min	Түр	MAX	Unit	CONDITIONS
Supply Voltage	VDD	3.0	3.3	3.6	V	
Supply current	IDD		20	25	mA	
Input Digital High	VINH	2.0			V	
Input Digital Low	VINL			0.8	V	
Crystal Frequency		15		40	MHz	Crystal Jitter < 1 ps p-p
Power on Calibration time				5	ms	After VDD reaches 2.8VNote: calibration time = 16,000 clock cycles
Max Frequency	FOUT	250		325	MHz	312 MHz nominal FOUT
Rise time	TR			300	ps	CL = 5pF, RL = 100Ω
Fall Time	TF			300	ps	CL = 5pF, RL = 100Ω
Duty cycle		45		55	%	LVDS output
Output skew				10	ps	Differential
Output Loading			100		Ω	
Output voltage		-400		400	mV	Differential (OUTP-OUTN)
Common Mode Voltage	VCM		1.2		V	
Output short circuit current			-5.7	-8	mA	Current limit to ground, VDD or Vp to Vn
Output Jitter, Cycle-to- cycle			6	10	ps	rms, at 312 MHz, Input referred
Output Jitter, Accumulated			16	20	ps	rms, over 1,000 cycles, at 312 MHz
Crystal Frequency Range		15		40	MHz	Fundamental Mode Crystal





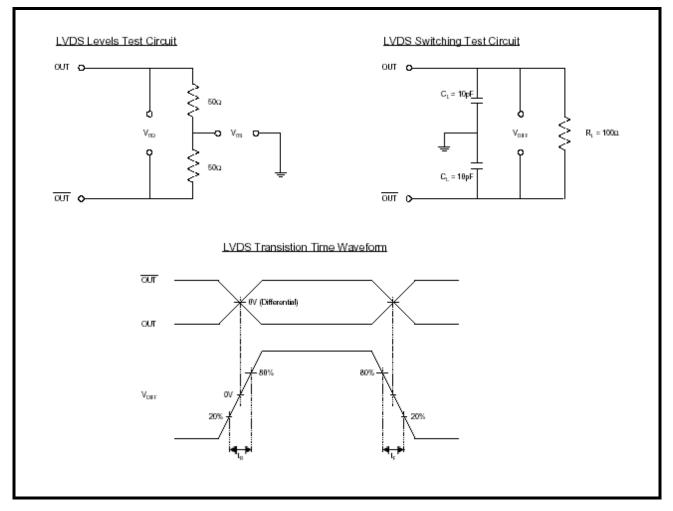


TABLE 1: FREQUENCY SELECTION TABLE

FS0Pin 10	FS1Pin 9	CRYSTAL FREQUENCY	INTERNAL CAPACITOR	MULTIPLY RATIO	OUTPUT DIVIDE	FREQUENCY OUTPUT
1	1	39.0 MHz	12 pF	8x	1	312 MHz
0	1	39.0 MHz	12 pF	8x	2	156 MHz
1	0	19.5 MHz	20 pF	16x	1	312 MHz
0	0	19.5 MHz	20 pF	16x	2	156 MHz
Notes:	1	1	1	1		1

1. Use Parallel Fundamental mode crystal

- 2. FS0 has a $50K\Omega$ pull-up resistor to VDD on chip
- 3. FS1 has a $50K\Omega$ pull-down resistor to ground on chip



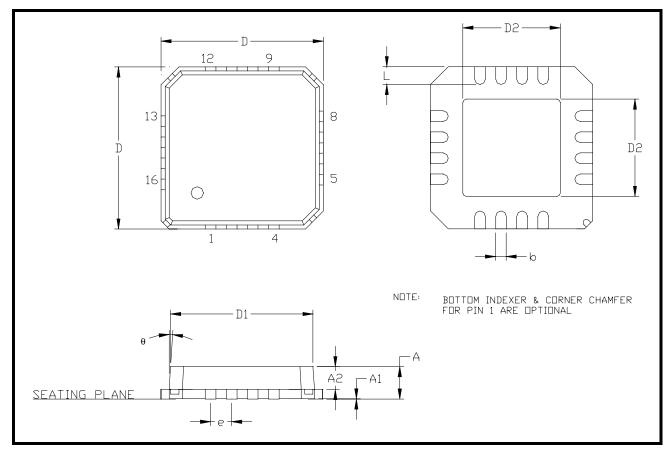
TABLE 2: POWER-DOWN AND OUTPUT TRI-STATE SELECTION TABLE

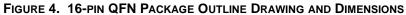
PD PIN 8	OE PIN 7	Status	Notes
1	Х	Outputs tri-stated and chip Powered-down	"X" = don't care
0	1		PD and OE have a 50K $arOmega$ pull-down resistor to ground on chip

ORDERING INFORMATION

PART NUMBER	PACKAGE TYPE	OPERATING TEMPERATURE RANGE
XRT8010IL	16 LEAD QUAD FLAT NO LEAD	-40°C to +85°C
	(4 mm x 4 mm, QFN)	







Note: The control dimension is in millimeter.

SYMBOL	INCI	HES	MILLIMETERS		
	MIN	MAX	MIN	MAX	
Α	0.031	0.039	0.80	1.00	
A1	0.000	0.002	0.00	0.05	
A2	0.000	0.039	0.00	1.00	
D	0.154	0.161	3.90	4.10	
D1	0.144	0.152	3.65	3.85	
D2	0.030	0.089	0.75	2.25	
b	0.009	0.015	0.23	0.38	
е	0.0256	BSC	0.65 BSC		
L	0.014	0.030	0.35	0.75	
θ	0°	12°	0°	12°	

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REV. P1.0.0

NOTES

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